

FDD5N50NZF

N-Channel UniFET™ FRFET® MOSFET 500 V, 3.7 A, 1.75 Ω

Features

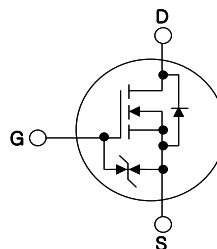
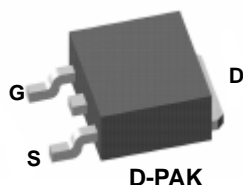
- $R_{DS(on)} = 1.47 \Omega$ (Typ.) @ $V_{GS} = 10 V$, $I_D = 1.85 A$
- Low Gate Charge (Typ. 9n C)
- Low C_{rss} (Typ. 4 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFET™ II MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. The body diode's reverse recovery performance of UniFET II FRFET® MOSFET has been enhanced by lifetime control. Its t_{rr} is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted*

Symbol	Parameter		FDD5N50NZF	Unit
V_{DSS}	Drain to Source Voltage		500	V
V_{GSS}	Gate to Source Voltage		± 25	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ C$)	3.7	A
		- Continuous ($T_C = 100^\circ C$)	2.2	
I_{DM}	Drain Current	- Pulsed (Note 1)	14	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		165	mJ
I_{AR}	Avalanche Current (Note 1)		3.3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		6.25	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		20	V/ns
P_D	Power Dissipation	($T_C = 25^\circ C$)	62.5	W
		- Derate above $25^\circ C$	0.5	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	$^\circ C$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDD5N50NZF	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD5N50NZF	FDD5N50NZFTM	D-PAK	380mm	16mm	2500

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$, $T_C = 25^\circ\text{C}$	500	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.5	-	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$, $V_{GS} = 0\text{V}$	-	-	10	μA
		$V_{DS} = 400\text{V}$, $V_{GS} = 0\text{V}$, $T_C = 125^\circ\text{C}$	-	-	100	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 25\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 10	μA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 1.85\text{A}$	-	1.47	1.75	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{V}$, $I_D = 1.85\text{A}$	-	4.2	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	365	485	pF
C_{oss}	Output Capacitance		-	50	65	pF
C_{rss}	Reverse Transfer Capacitance		-	4	8	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{V}$, $I_D = 3.7\text{A}$ $V_{GS} = 10\text{V}$ (Note 4)	-	9	12	nC
Q_{gs}	Gate to Source Gate Charge		-	2	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	4	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}$, $I_D = 3.7\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 25\Omega$ (Note 4)	-	12	35	ns
t_r	Turn-On Rise Time		-	19	50	ns
$t_{d(off)}$	Turn-Off Delay Time		-	31	70	ns
t_f	Turn-Off Fall Time		-	22	55	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3.7	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	14	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 3.7A	-	-	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 3.7A	-	87	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100A/μs	-	0.15	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 23\text{mH}$, $I_{AS} = 3.7\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 3.7\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

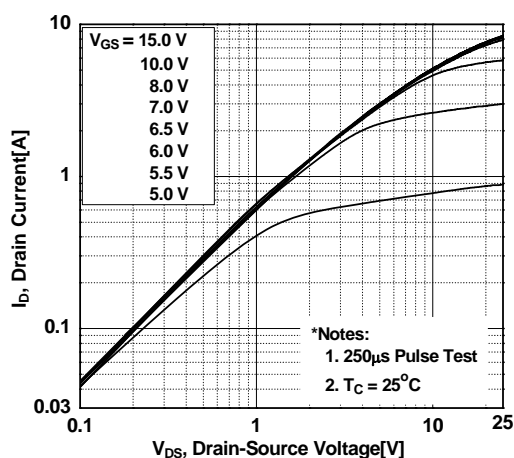


Figure 2. Transfer Characteristics

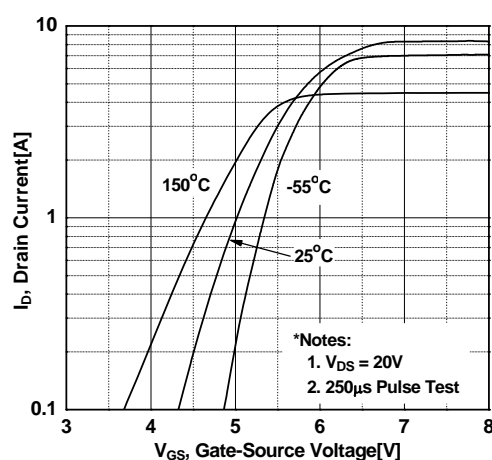


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

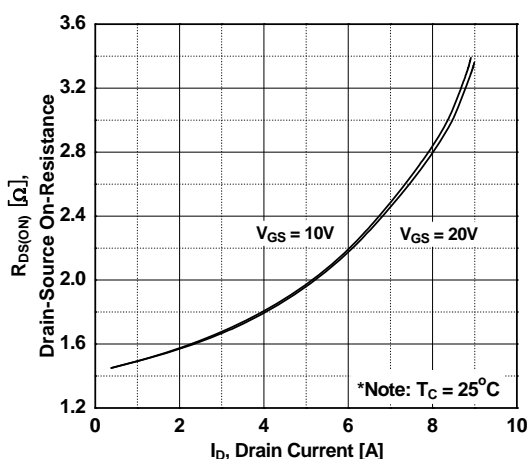


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

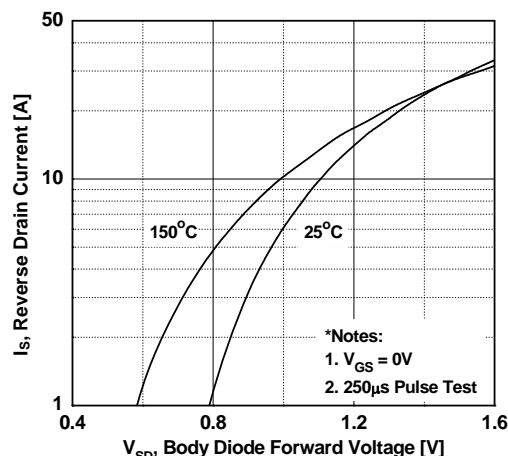


Figure 5. Capacitance Characteristics

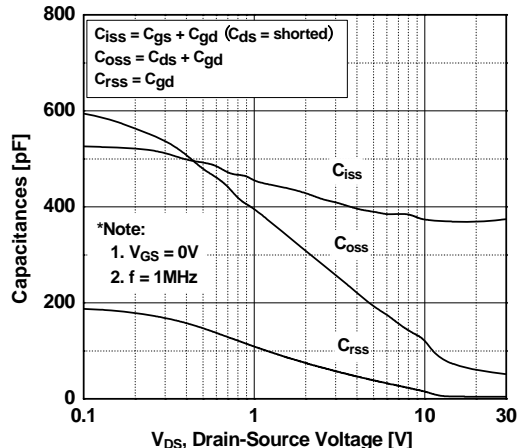
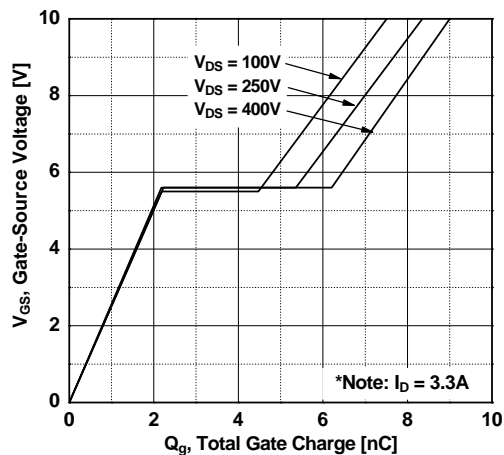


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

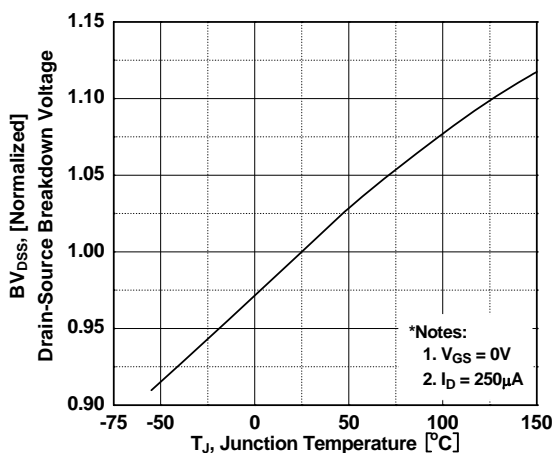


Figure 8. Maximum Safe Operating Area vs. Case Temperature

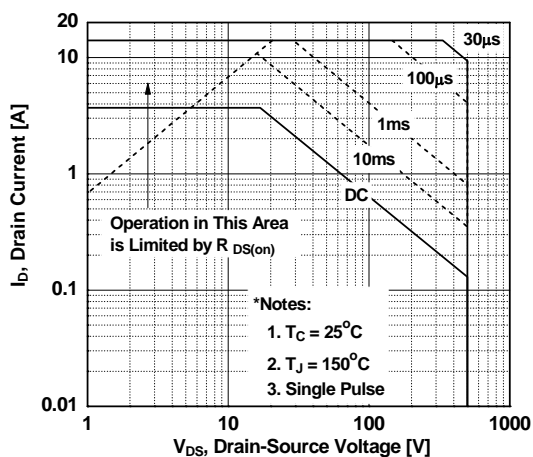


Figure 9. Maximum Drain Current

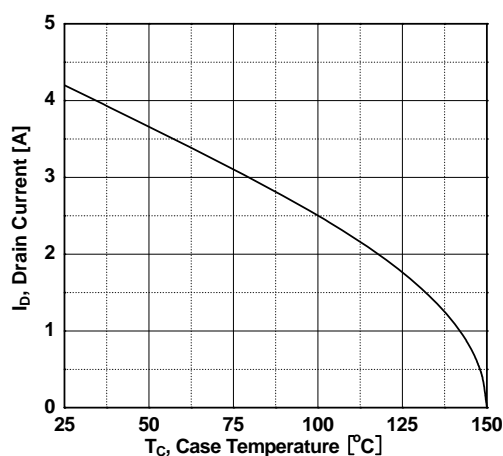
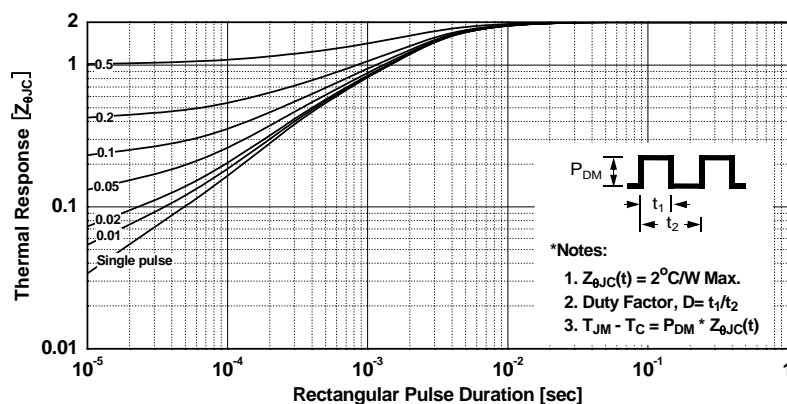


Figure 10. Transient Thermal Response Curve



Gate Charge Test Circuit & Waveform



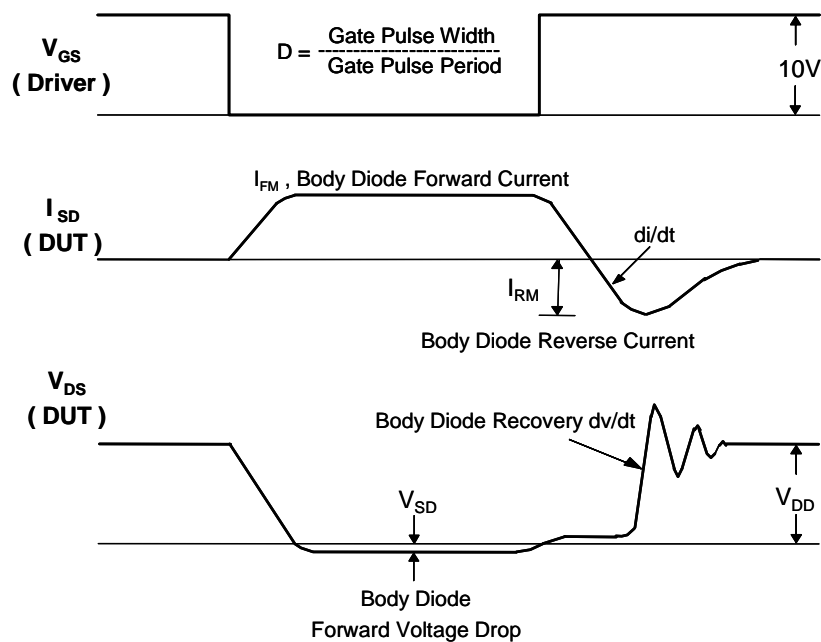
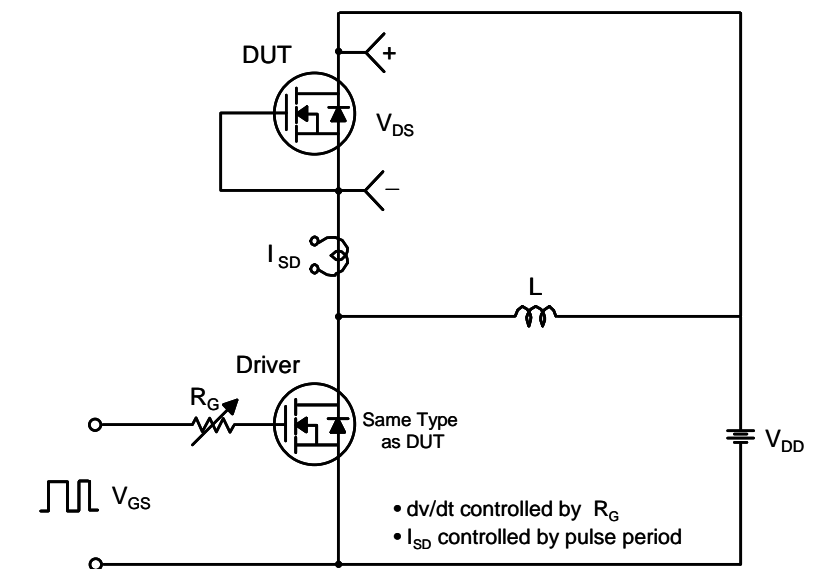
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

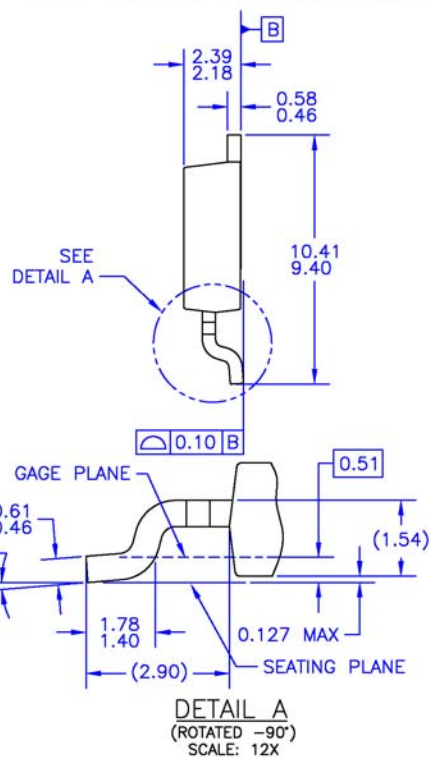
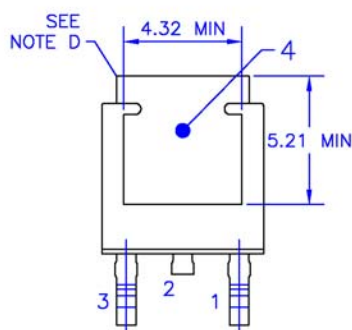
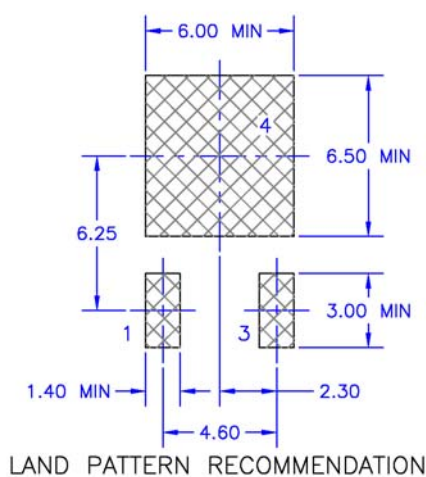
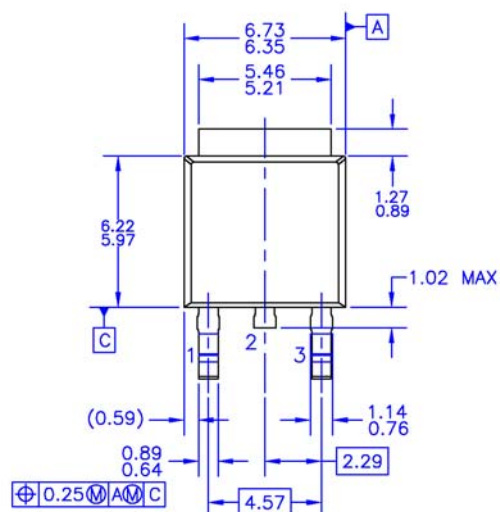


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

D-PAK




- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 - D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.
 - F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO220P1003X238-3N.
 - H) DRAWING NUMBER AND REVISION: MKT-T0252A03REV8



Dimensions in Millimeters

2Cool™
 AccuPower™
 AX-CAP®
 BitSiC™
 Build it Now™
 CorePLUS™
 CorePOWER™
 CROSSVOL™
 CTL™
 Current Transfer Logic™
 DEUXPEED®
 Dual Cool™
 EcoSPARK®
 EfficientMax™
 ESBC™
F®
 Fairchild®
 Fairchild Semiconductor®
 FACT Quiet Series™
 FACT®
 FAST®
 FastvCore™
 FFTBench™
 FPM™
 F-PFST™
 FRFET®
 Global Power ResourceSM
 Green Bridge™
 Green FPS™
 Green FPS™ e-Series™
 Gmax™
 GTO™
 IntelliMAX™
 ISOPLANAR™
 Marking Small Speakers Sound Louder
 and Better™
 MegaBuck™
 MICROCOUPLER™
 MicroFET™
 MicroPak™
 MicroPak2™
 MillerDrive™
 MotionMax™
 mWSaver™
 OptoHiT™
 OPTOLOGIC®
 OPTOPLANAR®



PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™.3
SuperSOT™.6
SuperSOT™.8
SupreMOS®
SvncFET™



Sync-Lock™
 **SYSTEM[®]
 GENERAL**
 TinyBoost™
 TinyBuck™
 TinyCalc™
 TinyLogic®
 TINYOPTO™
 TinyPower™
 TinyPWM™
 TinyWire™
 TransiC®
 TriFault Detect™
 TRUECURRENT®
 µSerDes™
 **SerDes[®]**
 UHC™
 Ultra FRFET™
 UniFET™
 VCX™
 VisualMax™
 VoltagePlus™
 XSTM™

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